

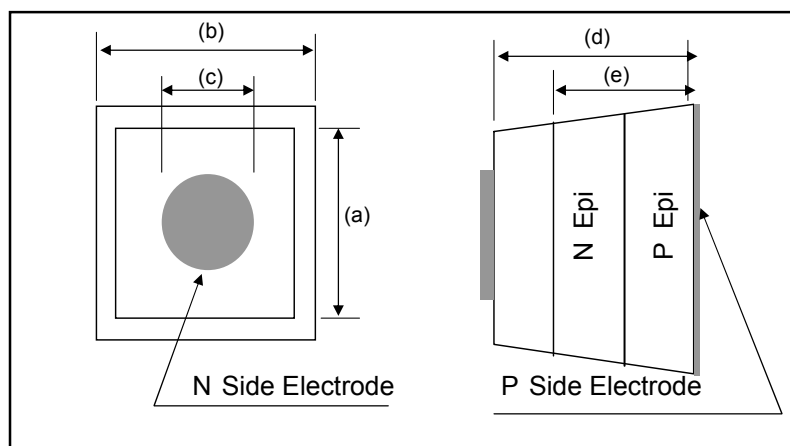
- 1. Material** Substrate GaAs (P Type)
Epitaxial Layer GaAlAs(N/P Type)
- 2. Electrode** N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy (Au/Sn Eutectic Metal)

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F		1.3	1.45	V	IF=30mA
Reverse Voltage	V_R	8			V	IR=10uA
Power	P_O	9	13		mW	IF=100mA
Wavelength	λ_P		920		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : Power is measured by Sorter E/T system with bare chip.

- 4. Mechanical Data**
- (a) Emission Area ----- 14mil x 14mil
 - (b) Bottom Area ----- 15mil x 15mil
 - (c) Bonding Pad ----- 130um
 - (d) Chip Thickness ----- 8.2mil
 - (e) Junction Height ----- 2mil



AUK Corp.

Eoyang factory, 513-5 Eoyang-dong, Iksan, 570-210, Korea
Tel. +82 63 839 1111 Fax. +82 63 835 8259

www.auk.co.kr

